Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
<b>L7</b>	1606	((CdS CdSe CdTe ZnS ZnSe ZnTe HgS HgSe HgTe GaN GaP GaAs InP InAs) or (cadmium zinc mercury) adj (sulfide selenide telluride) or (gallium indium) adj (nitride phosphide arsenide)) with (nanocrystal nanocrystalline nanocrystals quantum adj dots)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 10:40
L10	131	7 and (photocurable photosensitive curable) and ((CdS CdSe CdTe ZnS ZnSe ZnTe HgS HgSe HgTe GaN GaP GaAs InP InAs) or (cadmium zinc mercury) adj (sulfide selenide telluride) or (gallium indium) adj (nitride phosphide arsenide))	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 10:20
L11	6	(US-20040118448-\$ or US-20050051769-\$ or US-20040095658-\$).did_or (US-5434878-\$ or US-5253258-\$ or US-3984500-\$).did.	US-PGPUB; USPAT	OR	OFF	2006/04/17 10:20
L13	5	11 and ((CdS CdSe CdTe ZnS ZnSe ZnTe HgS HgSe HgTe GaN GaP GaAs InP InAs) or (cadmium zinc mercury) adj (sulfide selenide telluride) or (gallium indium) adj (nitride phosphide arsenide))	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 10:33
<b>L14</b>	17	(US-20030226498-\$ or US-20030170959-\$ or US-20030145779-\$ or US-20040039201-\$ or US-20050002635-\$ or US-20020155507-\$ or US-20020114998-\$ or US-20040115817-\$).did. or (US-6602671-\$ or US-6512172-\$ or US-6319426-\$ or US-6207392-\$ or US-5825790-\$ or US-5625456-\$ or US-5559057-\$ or US-5751018-\$). did.	US-PGPUB; USPAT	OR	OFF	2006/04/17 10:33
L15	15	14 and ((CdS CdSe CdTe ZnS ZnSe ZnTe HgS HgSe HgTe GaN GaP GaAs InP InAs) or (cadmium zinc mercury) adj (sulfide selenide telluride) or (gallium indium) adj (nitride phosphide arsenide))	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 12:04

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L16	2	14 not 15	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 10:34
L18	3	15 and (photocurable photocured cured photocuring curing curable)	US-PGPUB; USPAT;	OR	OFF	2006/04/17 10:37
-			EPO; DERWENT; IBM_TDB			
L21	10	Huynh with Wendy Milliron with Delia	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 10:39
L22	6	7 and 21	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 10:41
L23	. 6	7 and 21 and solvent	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 10:41
L24	7.	7 and (photocurable photocured photocuring)	US-PGPUB; USPAT; EPO;	OR	OFF	2006/04/17 10:48
			DERWENT; IBM_TDB			
L29	307	7 and (odpa topo MEH-PPV P3HT)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 11:12
L30	47	7 and (MEH-PPV P3HT)	US-PGPUB; USPAT;	OR	OFF	2006/04/17 11:12
			EPO; DERWENT; IBM_TDB			
L31	117	7 same (odpa topo)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 11:12
L32	38	7 same (odpa topo) and surfactant	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 11:13

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L36	3	(("5,448,582") or ("5,434,878") or ("6259506")).PN.	US-PGPUB; USPAT; USOCR	OR'	OFF	2006/04/17 11:54
L37	3	36 and (uv or light)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 11:54
L38	7	15 and uv	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 12:04
L39	365	semiconductor nanocrystal	US-PGPUB;	ADJ	OFF	2006/04/17 12:09
		There is a transfer of the state of the stat	USPAT		AU A	
L40	134	semiconductor nanocrystal.clm.	US-PGPUB; USPAT	ADJ	OFF	2006/04/17 12:09
L41	48	semiconductor nanocrystal with polymer	US-PGPUB; USPAT	ADJ	OFF	2006/04/17 12:09
L42	47	"5434878"	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 12:09
L43	38	("5,157,674" "5,233,621" "5,253, 258") and semiconductor	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17-12:09
L44	6	semiconductor nanocrystal same cur\$3	US-PGPUB; USPAT	ADJ	OFF	2006/04/17 12:09
L45	89	semiconductor adj nanocrystal and (cured curing curable)	US-PGPUB; USPAT	OR	ON	2006/04/17 12:09
L46	. 8	"6,114,038" and (cured curing curable)	US-PGPUB; USPAT	OR	ON	2006/04/17 12:09
L47	42	"6,114,038" and ligand	US-PGPUB; USPAT	OR	ON	2006/04/17 12:09
L48	36	"6096496".	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/04/17 12:09
L49	22	L45 and polymer with (cured curing curable)	US-PGPUB; USPAT	OR	ON	2006/04/17 12:09
L50	12	UV with (cured curing curable) with exposure adj level	US-PGPUB; USPAT	OR	ON	2006/04/17 12:09

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L51	1795	UV with (cured curing curable) with energy	US-PGPUB; USPAT	OR	ON	2006/04/17 12:09
L52	52	UV with (cured curing curable) with energy with level	US-PGPUB; USPAT	OR	ON	2006/04/17 12:09
L53	134	UV with (cured curing curable) with joule	US-PGPUB; USPAT	OR	ON	2006/04/17 12:09
L54	892	UV with (cured curing curable) with (millijoule mj joule)	US-PGPUB; USPAT	OR	ON	2006/04/17 12:09
L55	17	UV with (cured curing curable) with (millijoule mj joule) with polymer	US-PGPUB; USPAT	OR	ON	2006/04/17 12:09
L56	123	UV with (cured curing curable) with (millijoule mj joule) with resin	US-PGPUB; USPAT	OR	ON	2006/04/17 12:09
L57	6646	((257/40) or (428/447)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/17 12:09
L58	2	(("20050008880") or ("5178959")). PN	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/17 12:09
L59	32	Kunze-Klaus Haubrich-Scott Zurcher-Fabio Ridley-brent Rockenberger-Joerg	US-PGPUB	OR	ON	2006/04/17 12:09
L60	18	L59 and (nanoparticle nanocrystal)	US-PGPUB	OR	ON	2006/04/17 12:09
L61	54	acetophenone and benzoin and benzophenone and thioxantone	US-PGPUB; USPAT	OR	ON	2006/04/17 12:09
S18	53	("5,448,582" "5434878") and semiconductor	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 08:25
S22	92	semiconductor adj (microcrystallite microcrystal)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON .	2005/11/01 08:28